

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau

(43) International Publication Date
26 October 2023 (26.10.2023)



(10) International Publication Number
WO 2023/205001 A1

- (51) **International Patent Classification:**
H01J 37/305 (2006.01) *H01J 37/30* (2006.01)
- (21) **International Application Number:**
PCT/US2023/018168
- (22) **International Filing Date:**
11 April 2023 (11.04.2023)
- (25) **Filing Language:** English
- (26) **Publication Language:** English
- (30) **Priority Data:**
17/725,023 20 April 2022 (20.04.2022) US
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- (81) **Designated States** (*unless otherwise indicated, for every
kind of national protection available*): AE, AG, AL, AM,
AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ,
CA, CH, CL, CN, CO, CR, CU, CV, CZ, DE, DJ, DK, DM,
DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT,
HN, HR, HU, ID, IL, IN, IQ, IR, IS, IT, JM, JO, JP, KE, KG,
KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY,
MA, MD, MG, MK, MN, MU, MW, MX, MY, MZ, NA,
NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO,
RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH,
TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS,
ZA, ZM, ZW.

(54) **Title:** REDUCED CHARGING BY LOW NEGATIVE VOLTAGE IN FIB SYSTEMS

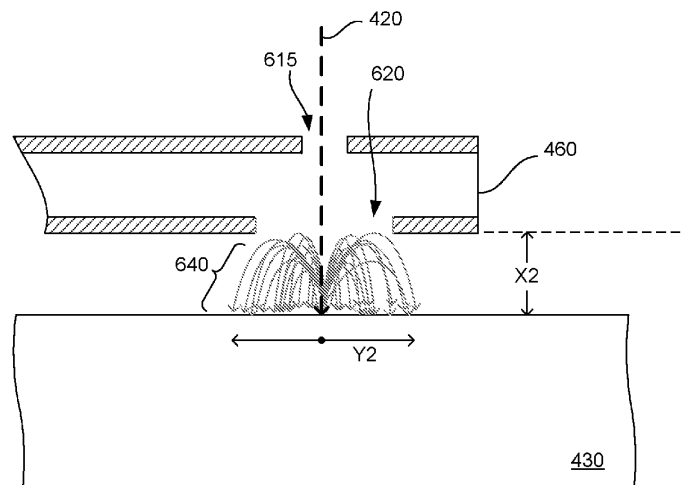


FIG. 6C

(57) **Abstract:** A method of processing a region of a sample, the method comprising: positioning a sample within a vacuum chamber; generating an ion beam with a focused ion beam (FIB) column; focusing the ion beam on the sample and scanning the focused ion beam across the region of the sample thereby generating secondary electrons that are ejected from a surface of the sample within the region; and during the scanning, applying a negative bias voltage to an electrically conductive structure proximate the region to alter a trajectory of the secondary electrons and repel the secondary electrons back to the sample surface, wherein the electrically conductive structure is one of a gas injection nozzle, a voltage pin or a nano-manipulator.

[Continued on next page]

WO 2023/205001 A1

(84) Designated States (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, CV, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SC, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, ME, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Published:

— with international search report (Art. 21(3))